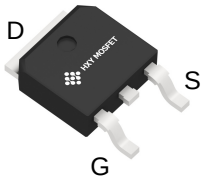
DMN39M1LK3-13

N-Channel Enhancement Mode MOSFET

Description

The DMN39M1LK3-13 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

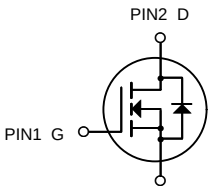


TO-252-2L (DPAK)

General Features

V_{DS} = 30V I_D = 120A

$R_{DS(ON)}$ < 3.8mΩ @ V_{GS}=10V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMN39M1LK3-13	TO-252-2L(DPAK)	HXY MOSFET	2500

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	120	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	75	A
I_{DM}	Pulsed Drain Current[2]	384	A
EAS	Single Pulse Avalanche Energy[3]	196	mJ
I_{AS}	Avalanche Current	53.8	A
P_D@T_C=25℃	Total Power Dissipation[4]	62.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	62	℃/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V	-	-	1	μA
		T_J=85°C	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	1.4	1.7	2.5	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$ [d]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=20A	-	3	3.8	mΩ
		T_J=125°C	-	4.4	-	
		V_{GS}=4.5V, I_{DS}=15A	-	4.0	5.5	
Gfs	Forward Transconductance	V_{DS}=5V, I_{DS}=10A	-	24.6	-	S
Diode Characteristics						
V_{SD} [d]	Diode Forward Voltage	I_{SD}=20A, V_{GS}=0V	-	0.8	1.1	V
t_{rr}	Reverse Recovery Time	I_{DS}=20A, dI_{SD}/dt=100A/μs	-	35.6	-	ns
t_a	Charge Time		-	19.3	-	
t_b	Discharge Time		-	16.3	-	
Q_{rr}	Reverse Recovery Charge		-	26	-	nC
Dynamic Characteristics [e]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz	-	1	2	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, Frequency=1.0MHz	-	2485	2971	pF
C_{oss}	Output Capacitance		-	850	-	
C_{rss}	Reverse Transfer Capacitance		-	85	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=15V, R_L=15Ω, I_{DS}=1A, V_{GEN}=10V, R_G=6Ω	-	12.4	23	ns
t_r	Turn-on Rise Time		-	9.5	18	
$t_{d(OFF)}$	Turn-off Delay Time		-	27.2	49	
t_f	Turn-off Fall Time		-	35.2	64	
Gate Charge Characteristics [e]						
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=10V, I_{DS}=20A	-	20.6	28.8	nC
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=4.5V, I_{DS}=20A	-	9.8	-	
Q_{gth}	Threshold Gate Charge		-	1.8	-	
Q_{gs}	Gate-Source Charge		-	3.8	-	
Q_{gd}	Gate-Drain Charge		-	3.7	-	

Note d：Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note e：Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

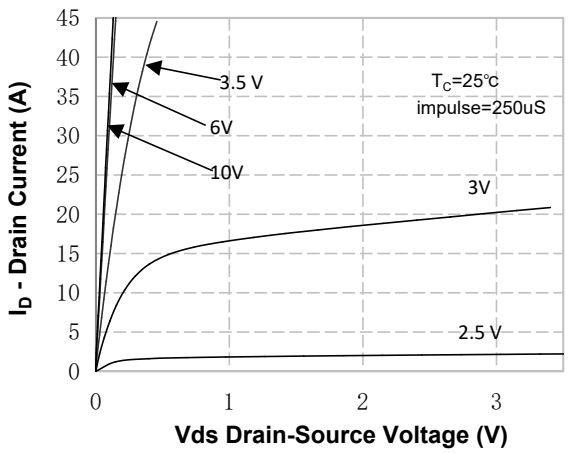


Figure 1. On-Region Characteristics

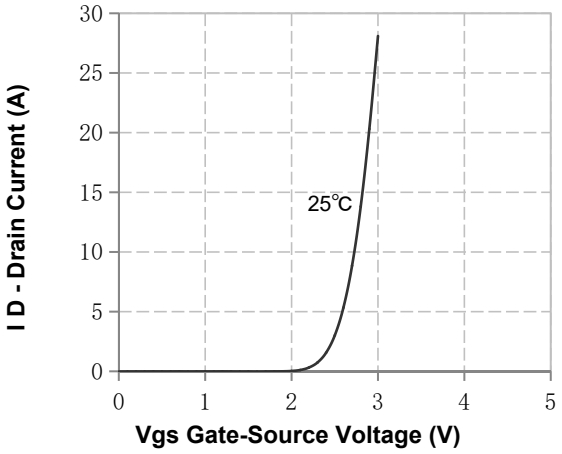


Figure 2. Transfer Characteristics

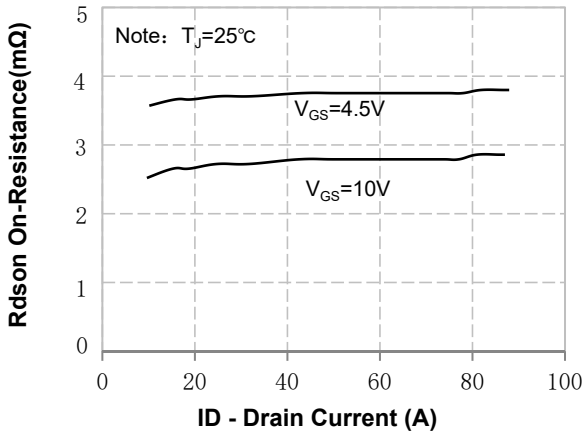


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

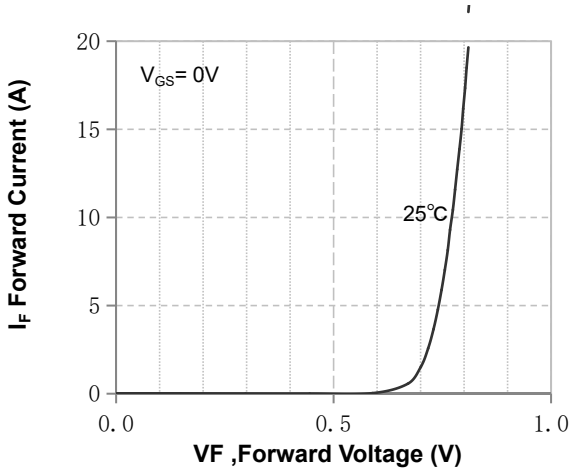


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

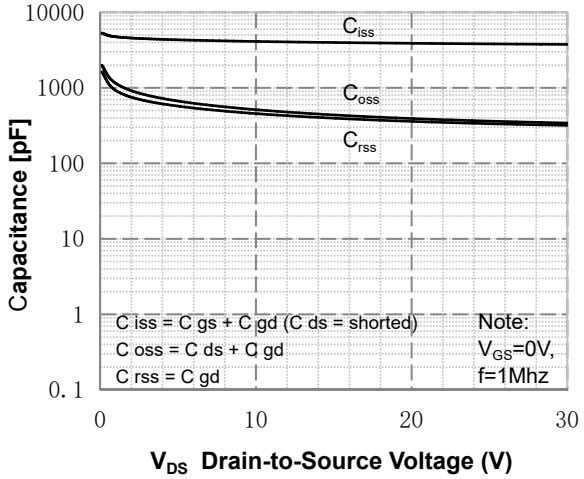


Figure 5. Capacitance Characteristics

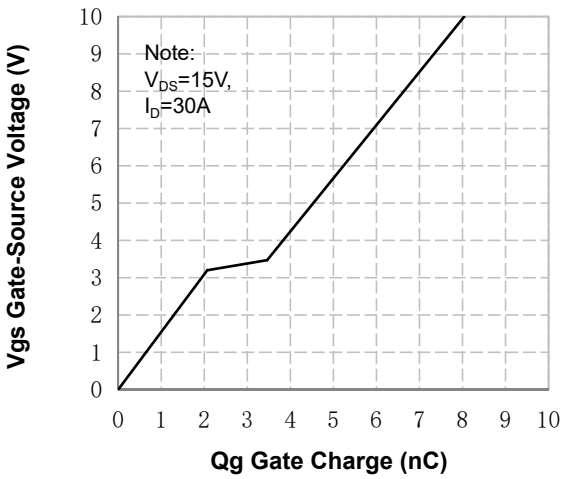


Figure 6. Gate Charge Characteristics

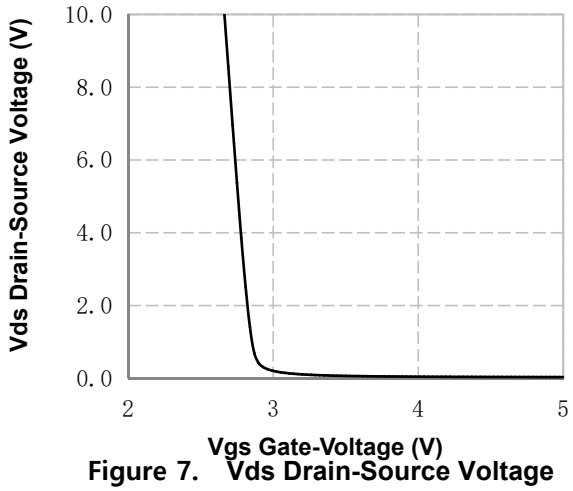


Figure 7. Vds Drain-Source Voltage vs Gate Voltage

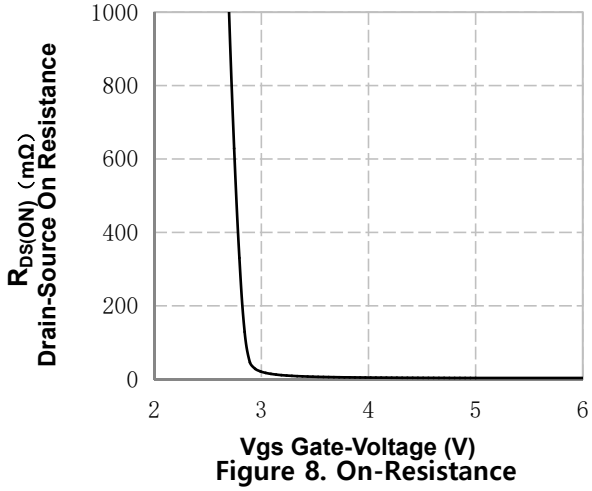


Figure 8. On-Resistance vs Gate Voltage

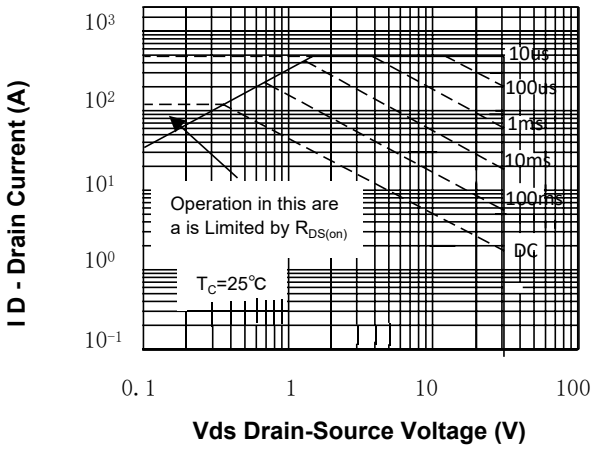


Figure 9. Maximum Safe Operating Area

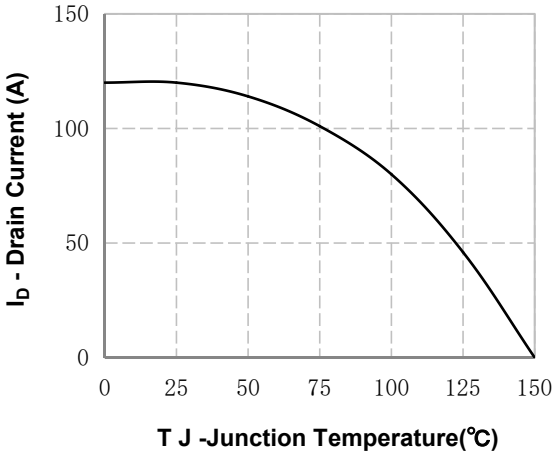


Figure 10. Maximum Continuous Drain Current vs Temperature

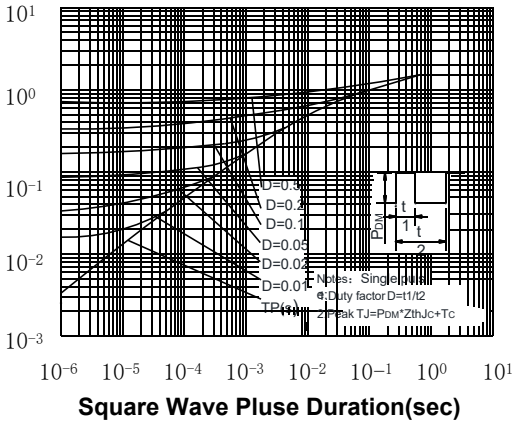
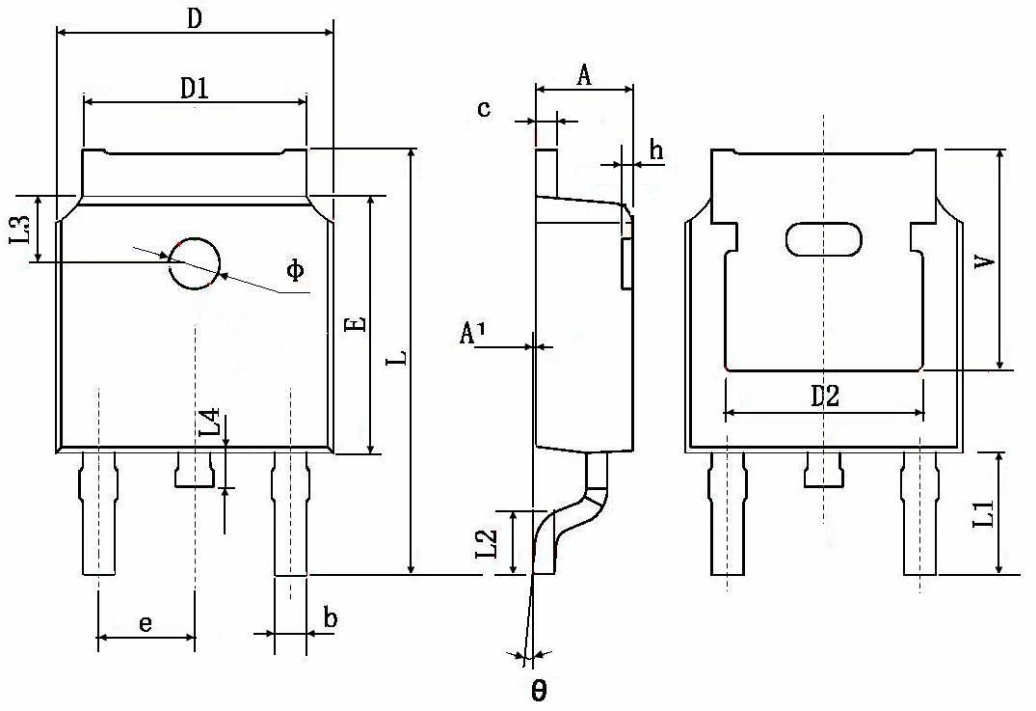


Figure 11. Transient Thermal Response Curve

TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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